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## BYV255V

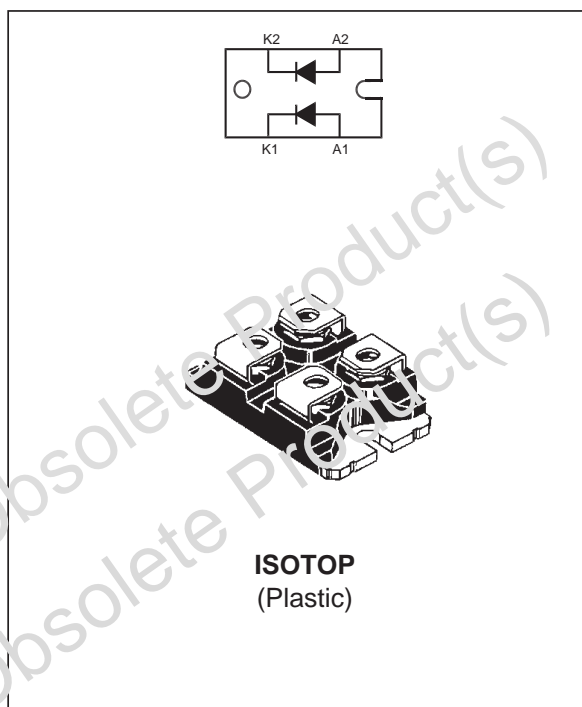
### HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

#### FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED :  
 Insulating voltage = 2500 V<sub>RMS</sub>  
 Capacitance = 55 pF

#### DESCRIPTION

Dual rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in ISOTOP™ this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
I <sub>F(RMS)</sub>	RMS forward current	Per diode	150	A
I <sub>F(AV)</sub>	Average forward current $\delta = 0.5$	T <sub>c</sub> =110°C Per diode	100	A
I <sub>FSM</sub>	Surge non repetitive forward current	tp=10ms sinusoidal Per diode	1600	A
T <sub>stg(j)</sub>	Storage and junction temperature range		- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	200	V

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### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case	Per diode	0.4
		Total	0.25
			°C/W
Rth (c)	Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

### ELECTRICAL CHARACTERISTICS (Per diode) STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			100	μA
	T <sub>j</sub> = 100°C				10	mA
V <sub>F</sub> **	T <sub>j</sub> = 125°C	I <sub>F</sub> = 100 A			0.85	V
	T <sub>j</sub> = 125°C	I <sub>F</sub> = 200 A			1.00	
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 200 A			1.15	

Pulse test : \* tp = 5 ms, duty cycle < 2 %

\*\* tp = 380 μs, duty cycle < 2 %

### RECOVERY CHARACTERISTICS

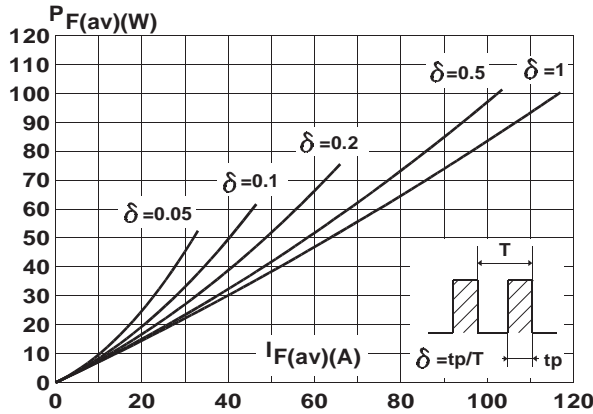
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
trr	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 0.5A I <sub>R</sub> = 1A	I <sub>rr</sub> = 0.25A			55	ns
		I <sub>F</sub> = 1A V <sub>R</sub> = 30V	di <sub>F</sub> /dt = -50A/μs			80	
t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A V <sub>FR</sub> = 1.1 x V <sub>F</sub>	tr = 5 ns		10		ns
V <sub>FP</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	tr = 5 ns		1.5		V

### TURN-OFF SWITCHING CHARACTERISTICS

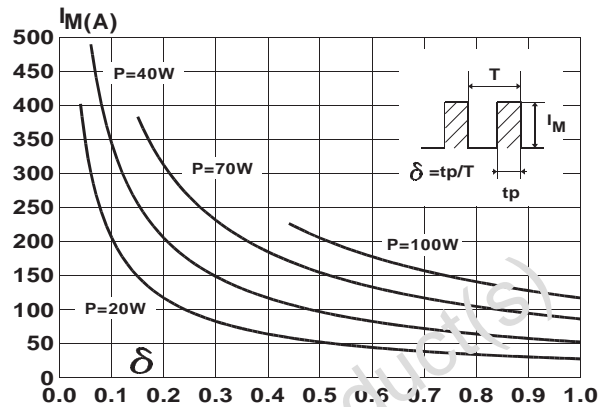
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I <sub>RM</sub>	T <sub>j</sub> = 100°C	I <sub>F</sub> = 100A L <sub>p</sub> ® 0.05μH V <sub>CC</sub> ® 0.6 V <sub>RRM</sub>	di <sub>F</sub> /dt = -200A/μs			16	A
			di <sub>F</sub> /dt = -400A/μs		24		

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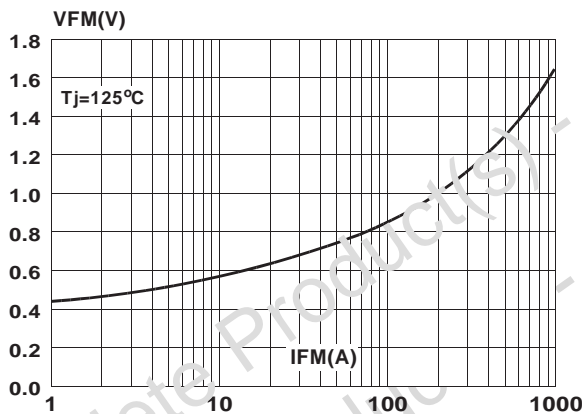
**Fig.1** : Average forward power dissipation versus average forward current.



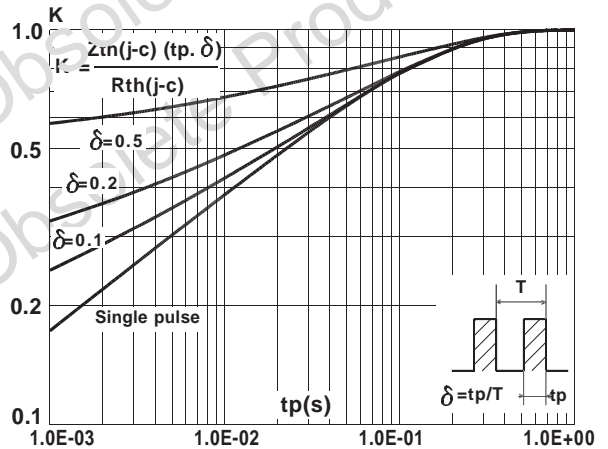
**Fig.2** : Peak current versus form factor.



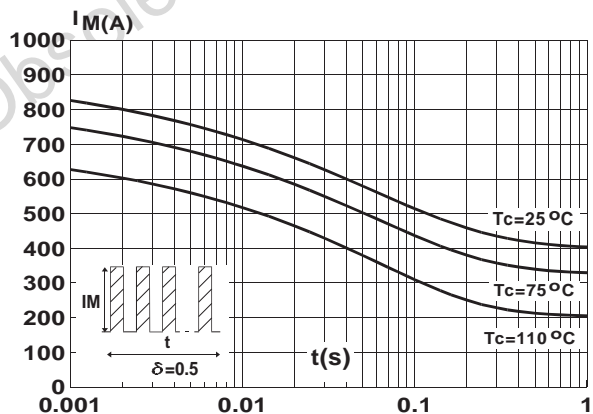
**Fig.3** : Forward voltage drop versus forward current (maximum values).



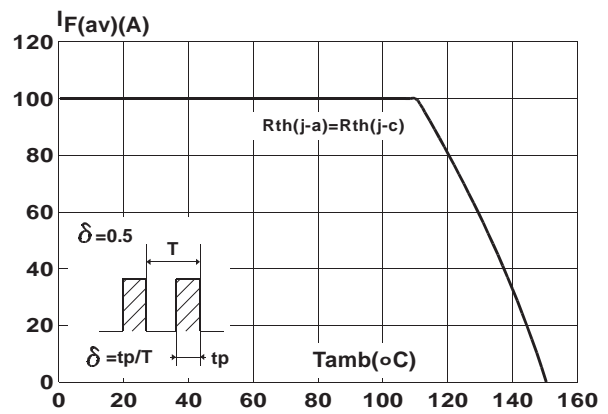
**Fig.4** : Relative variation of thermal impedance junction to case versus pulse duration.



**Fig.5** : Non repetitive surge peak forward current versus overload duration.

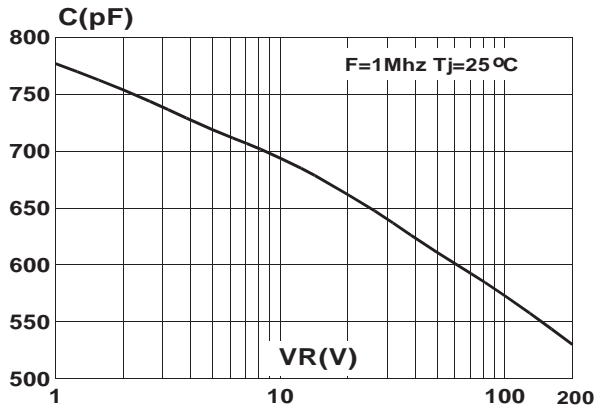


**Fig.6** : Average current versus ambient temperature. (duty cycle : 0.5)

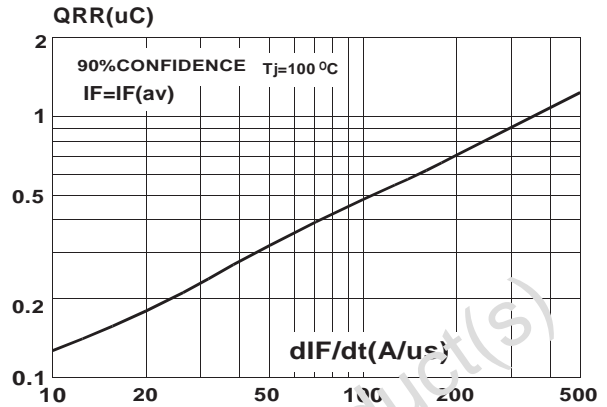


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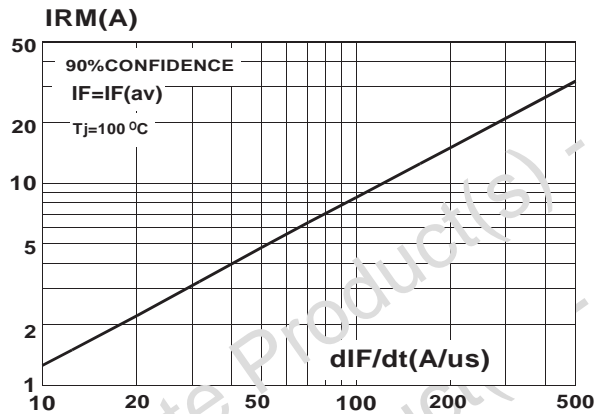
**Fig.7 :** Junction capacitance versus reverse voltage applied (Typical values).



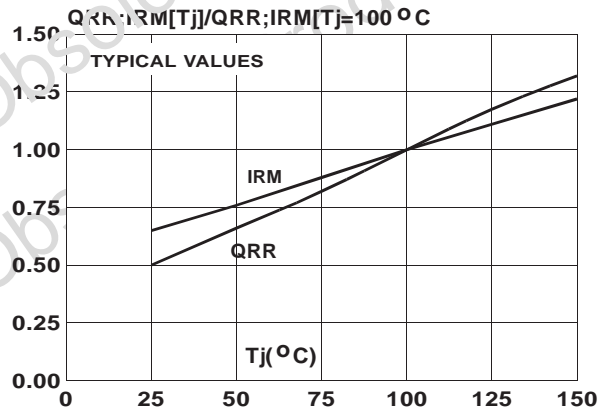
**Fig.8 :** Recovery charges versus  $dI_F/dt$ .



**Fig.9 :** Peak reverse current versus  $dI_F/dt$ .



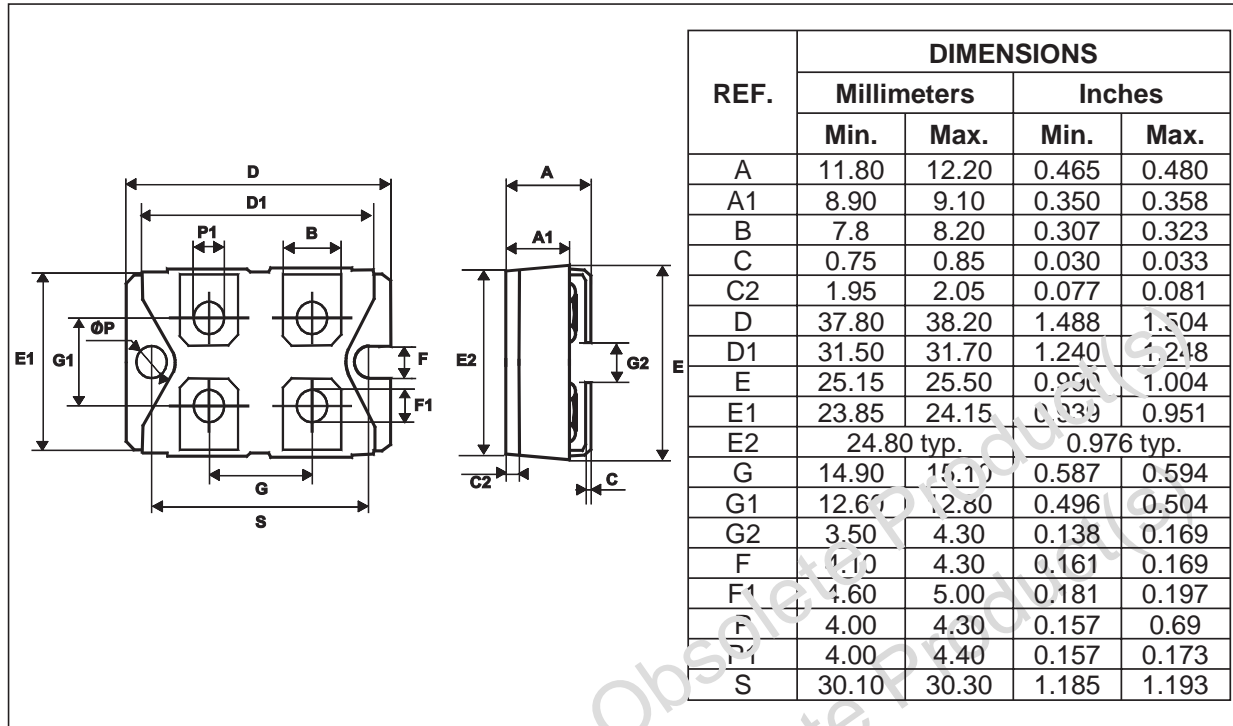
**Fig.10 :** Dynamic parameters versus junction temperature.



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**PACKAGE MECHANICAL DATA**

**ISOTOP**



- **Marking** : Type number
- Cooling method : C
- Weight : 27 g
- Epoxy meets UL94, V0

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